

Docket No.: 57454-979

**PATENT**

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Application of	:	Customer Number: 20277
	:	
Hideto HIDAKA	:	Confirmation Number:
	:	
Serial No.: Continuation of Appl. No.		
10/234,243	:	Group Art Unit:
	:	
Filed: October 24, 2003	:	Examiner:
	:	
For:		THIN FILM MAGNETIC MEMORY DEVICE FOR PROGRAMMING REQUIRED
		INFORMATION WITH AN ELEMENT SIMILAR TO A MEMORY CELL AND
		INFORMATION PROGRAMMING METHOD

**INFORMATION DISCLOSURE STATEMENT**

Mail Stop Patent Application  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Dear Sir:

In accordance with the provisions of 37 C.F.R. 1.56, 1.97 and 1.98, the attention of the Patent and Trademark Office is hereby directed to the references listed on the attached form PTO-1449. It is respectfully requested that the references be expressly considered during the prosecution of this application, and that the references be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

This Information Disclosure Statement is being filed within three months of the U.S. filing date OR before the mailing date of a first Office Action on the merits. No certification or fee is required.

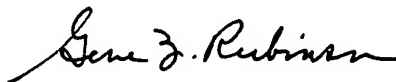
Continuation of Appl. No.  
10/234,243

The references were cited by or submitted to the U.S. Patent and Trademark Office in parent application Serial No. 10/234,243, filed September 5, 2002, which is relied upon for an earlier filing date under 35 USC 120. Thus, copies of these references are not attached. 37 CFR 1.98(d).

Please charge any shortage in fees due in connection with the filing of this paper, including extension of time fees, to Deposit Account 500417 and please credit any excess fees to such deposit account.

Respectfully submitted,

MCDERMOTT, WILL & EMERY

A handwritten signature in cursive script that reads "Gene Z. Robinson".

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INFORMATION DISCLOSURE CITATION IN AN APPLICATION  (PTO-1449)				ATTY. DOCKET NO. 57454-979		SERIAL NO. Continuation of Appl. No. 10/234,243	
				APPLICANT Hideto HIDAKA			
				FILING DATE October 24, 2003		GROUP	
U.S. PATENT DOCUMENTS							
EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Code <sup>2</sup> (if known)		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	
		US	6,324,093 B1	11/27/2001	Perner et al.		
		US	6,331,943 B1	12/18/2001	Naji et al.		
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FOREIGN PATENT DOCUMENTS							
EXAMINER'S INITIALS	CITE NO.	Foreign Patent Document Country Codes -Number 4 -Kind Codes (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Figures Appear	Translation	
						Yes	No
OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)							
EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.					
		"A 10 ns Read and Write Non-Volatile Memory Array Using a Magnetic Tunnel Junction and FET Switch in Each Cell", SCHEUERLEIN et al., ISSCC Digest of Technical Papers, TA7.2, Feb. 2000, pp. 94-95, 128-129, 409-410					
		"Nonvolatile RAM based on Magnetic Tunnel Junction Elements", DURLAM et al., ISSCC Digest of Technical Papers, TA7.3, Feb. 2000, pp. 96-97, 130-131, 410-411					
		A 256kb 3.0V 1T1MTJ Nonvolatile Magnetoresistive RAM", NAJI et al., ISSCC Digest of Technical Papers, TA7.6, Feb. 2001, pp. 94-95, 122-123, 404-405, 438					
EXAMINER				DATE CONSIDERED			

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.